# Octal 3-State Noninverting Buffer/Line Driver/Line Receiver

# **High-Performance Silicon-Gate CMOS**

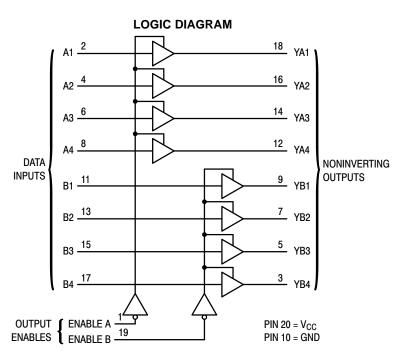
The MC74HC244A is identical in pinout to the LS244. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

This octal noninverting buffer/line driver/line receiver is designed to be used with 3-state memory address drivers, clock drivers, and other bus-oriented systems. The device has noninverting outputs and two active-low output enables.

The HC244A is similar in function to the HC240A.

#### **Features**

- Output Drive Capability: 15 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No. 7 A
- Chip Complexity: 136 FETs or 34 Equivalent Gates
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant





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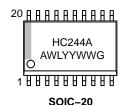


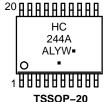
SOIC-20 DW SUFFIX CASE 751D TSSOP-20 DT SUFFIX CASE 948E

#### **PIN ASSIGNMENT**

ENABLE A	1●	20	v <sub>cc</sub>
A1 [	2	19	ENABLE B
YB4 [	3	18	YA1
A2 [	4	17	B4
YB3 [	5	16	YA2
A3 [	6	15	B3
YB2 [	7	14	YA3
A4 [	8	13	B2
YB1	9	12	YA4
GND [	10	11	] В1

#### MARKING DIAGRAMS





A = Assembly Location

WL, L = Wafer Lot YY, Y = Year WW, W = Work Week G or ■ = Pb-Free Package

(\*Note: Microdot may be in either location)

#### **FUNCTION TABLE**

Inpu	Outputs	
Enable A, Enable B	A, B	YA, YB
L	L	L
L	Н	Н
Н	Χ	Z

Z = high impedance

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

#### **MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)	-0.5 to +7.0	V
V <sub>in</sub>	DC Input Voltage (Referenced to GND)	$-0.5$ to $V_{CC} + 0.5$	V
V <sub>out</sub>	DC Output Voltage (Referenced to GND)	$-0.5$ to $V_{CC} + 0.5$	V
I <sub>in</sub>	DC Input Current, per Pin	±20	mA
I <sub>out</sub>	DC Output Current, per Pin	±35	mA
Icc	DC Supply Current, V <sub>CC</sub> and GND Pins	±75	mA
I <sub>IK</sub>	Input Clamp Current (V <sub>I</sub> < 0 or V <sub>I</sub> > V <sub>CC</sub> )	±20	mA
I <sub>OK</sub>	Output Clamp Current (V <sub>O</sub> < 0 or V <sub>O</sub> > V <sub>CC</sub> )	±20	mA
P <sub>D</sub>	Power Dissipation in Still Air, SOIC Package† TSSOP Package†	500 450	mW
T <sub>stg</sub>	Storage Temperature	-65 to +150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds (SOIC, SSOP or TSSOP Package)	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation,  $V_{in}$  and  $V_{out}$  should be constrained to the range GND  $\leq$  ( $V_{in}$  or  $V_{out}$ )  $\leq$   $V_{CC}$ .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or  $V_{CC}$ ). Unused outputs must be left open.

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

†Derating: SOIC Package: –7 mW/°C from 65° to 125°C TSSOP Package: –6.1 mW/°C from 65° to 125°C

#### RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Max	Unit
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)		2.0	6.0	V
V <sub>in</sub> , V <sub>out</sub>	DC Input Voltage, Output Voltage (Referenced to GND)		0	V <sub>CC</sub>	V
T <sub>A</sub>	Operating Temperature, All Package Types		<del>-</del> 55	+125	°C
t <sub>r</sub> , t <sub>f</sub>	(Figure 1) V <sub>CC</sub>	c = 2.0 V c = 4.5 V c = 6.0 V	0 0 0	1000 500 400	ns

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

### DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Gu	aranteed Li	mit	
Symbol	Parameter	Test Conditions	V <sub>CC</sub>	–55 to 25°C	≤ 85°C	≤ 125°C	Unit
V <sub>IH</sub>	Minimum High-Level Input Voltage	$\begin{aligned} V_{out} &= V_{CC} - 0.1 \text{ V} \\  I_{out}  &\leq 20  \mu\text{A} \end{aligned}$	2.0 3.0 4.5 6.0	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	V
V <sub>IL</sub>	Maximum Low-Level Input Voltage	$\begin{aligned} V_{out} &= 0.1 \text{ V} \\  I_{out}  &\leq 20  \mu\text{A} \end{aligned}$	2.0 3.0 4.5 6.0	0.5 0.9 1.35 1.8	0.5 0.9 1.35 1.8	0.5 0.9 1.35 1.8	V
V <sub>OH</sub>	Minimum High-Level Output Voltage	$\begin{aligned} &V_{in} = V_{IH} \\ & I_{out}  \leq 20 \; \mu A \end{aligned}$	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		$ \begin{aligned} V_{in} &= V_{IH} & \mid I_{out} \mid \leq 2.4 \text{ mA} \\ \mid I_{out} \mid \leq 6.0 \text{ mA} \\ \mid I_{out} \mid \leq 7.8 \text{ mA} \end{aligned} $	3.0 4.5 6.0	2.48 3.98 5.48	2.34 3.84 5.34	2.2 3.7 5.2	
V <sub>OL</sub>	Maximum Low–Level Output Voltage	$ \begin{aligned} & V_{in} = V_{IL} \\ &  I_{out}  \le 20 \ \mu A \end{aligned} $	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		$ \begin{aligned} V_{in} = V_{IL} & \mid I_{Out} \mid \leq 2.4 \text{ mA} \\ \mid I_{Out} \mid \leq 6.0 \text{ mA} \\ \mid I_{Out} \mid \leq 7.8 \text{ mA} \end{aligned} $	3.0 4.5 6.0	0.26 0.26 0.26	0.33 0.33 0.33	0.4 0.4 0.4	
l <sub>in</sub>	Maximum Input Leakage Current	V <sub>in</sub> = V <sub>CC</sub> or GND	6.0	±0.1	±1.0	±1.0	μΑ
l <sub>OZ</sub>	Maximum Three–State Leakage Current	Output in High-Impedance State $V_{in} = V_{IL}$ or $V_{IH}$ $V_{out} = V_{CC}$ or GND	6.0	±0.5	±5.0	±10	μΑ
Icc	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC}$ or GND $I_{out} = 0 \mu A$	6.0	4.0	40	160	μΑ

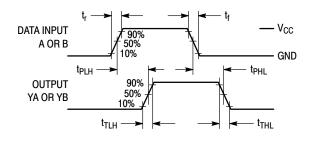
# AC ELECTRICAL CHARACTERISTICS (C $_{L}$ = 50 pF, Input $t_{r}$ = $t_{f}$ = 6 ns)

			Gu	aranteed Li	mit	
Symbol	Parameter	V <sub>CC</sub>	–55 to 25°C	≤85°C	≤125°C	Unit
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, A to YA or B to YB (Figures 1 and 3)	2.0 3.0 4.5 6.0	96 50 18 15	115 60 23 20	135 70 27 23	ns
t <sub>PLZ</sub> , t <sub>PHZ</sub>	Maximum Propagation Delay, Output Enable to YA or YB (Figures 2 and 4)	2.0 3.0 4.5 6.0	110 60 22 19	140 70 28 24	165 80 33 28	ns
t <sub>PZL</sub> , t <sub>PZH</sub>	Maximum Propagation Delay, Output Enable to YA or YB (Figures 2 and 4)	2.0 3.0 4.5 6.0	110 60 22 19	140 70 28 24	165 80 33 28	ns
t <sub>TLH</sub> , t <sub>THL</sub>	Maximum Output Transition Time, Any Output (Figures 1 and 3)	2.0 3.0 4.5 6.0	60 23 12 10	75 27 15 13	90 32 18 15	ns
C <sub>in</sub>	Maximum Input Capacitance	-	10	10	10	pF
C <sub>out</sub>	Maximum Three–State Output Capacitance (Output in High–Impedance State)	_	15	15	15	pF

		Typical @ 25°C, V <sub>CC</sub> = 5.0 V	
$C_{PD}$	Power Dissipation Capacitance (Per Buffer)*	34	pF

<sup>\*</sup> Used to determine the no–load dynamic power consumption:  $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$ .

#### **SWITCHING WAVEFORMS**

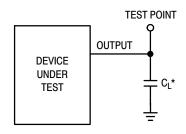


 $V_{\text{CC}}$ **ENABLE** 50% GND A OR B t<sub>PZL</sub>  $t_{PLZ}$ HIGH **IMPEDANCE** 50% **OUTPUT Y** 10%  $V_{OL}$  $t_{PZH}$  $t_{PHZ}$ 90%  $V_{OH}$ . 50% **OUTPUT Y** HIGH **IMPEDANCE** 

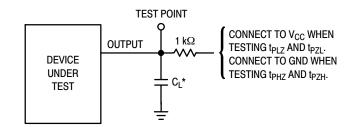
Figure 1.

Figure 2.

#### **TEST CIRCUITS**



\*Includes all probe and jig capacitance



\*Includes all probe and jig capacitance

Figure 3. Test Circuit

Figure 4. Test Circuit

#### **PIN DESCRIPTIONS**

#### **INPUTS**

A1, A2, A3, A4, B1, B2, B3, B4 (Pins 2, 4, 6, 8, 11, 13, 15, 17)

Data input pins. Data on these pins appear in noninverted form on the corresponding Y outputs, when the outputs are enabled.

### **CONTROLS**

#### Enable A, Enable B (Pins 1, 19)

Output enables (active-low). When a low level is applied to these pins, the outputs are enabled and the devices

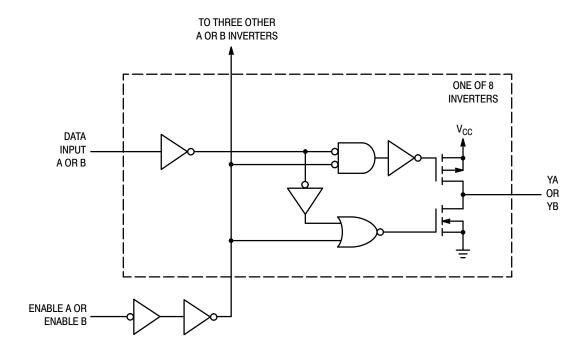
function as noninverting buffers. When a high level is applied, the outputs assume the high impedance state.

### **OUTPUTS**

YA1, YA2, YA3, YA4, YB1, YB2, YB3, YB4 (Pins 18, 16, 14, 12, 9, 7, 5, 3)

Device outputs. Depending upon the state of the output–enable pins, these outputs are either noninverting outputs or high–impedance outputs.

#### **LOGIC DETAIL**



#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MC74HC244ADWG	SOIC-20 WIDE (Pb-Free)	38 Units / Rail
MC74HC244ADWR2G	SOIC-20 WIDE (Pb-Free)	1000 / Tape & Reel
MC74HC244ADTG	TSSOP-20 (Pb-Free)	75 Units / Rail
MC74HC244ADTR2G	TSSOP-20 (Pb-Free)	2500 / Tape & Reel
NLV74HC244ADWR2G*	SOIC-20 WIDE (Pb-Free)	1000 / Tape & Reel
NLV74HC244ADTR2G*	TSSOP-20 (Pb-Free)	2500 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
\*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q100 Qualified and PPAP

Capable

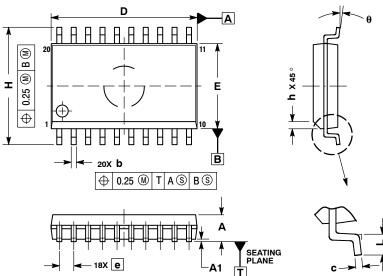




SOIC-20 WB CASE 751D-05 **ISSUE H** 

**DATE 22 APR 2015** 

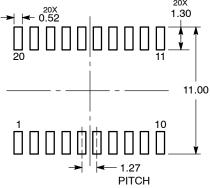




- DIMENSIONS ARE IN MILLIMETERS.
   INTERPRET DIMENSIONS AND TOLERANCES.
- PER ASME Y14.5M, 1994.
  3. DIMENSIONS D AND E DO NOT INCLUDE MOLD
- PROTRUSION.
  MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
- DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL

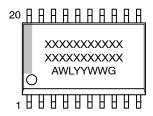
	MILLIMETERS		
DIM	MIN	MAX	
Α	2.35	2.65	
A1	0.10	0.25	
b	0.35	0.49	
С	0.23	0.32	
D	12.65	12.95	
E	7.40	7.60	
е	1.27	BSC	
Н	10.05	10.55	
h	0.25	0.75	
L	0.50	0.90	
A	0 °	7 °	

#### **RECOMMENDED SOLDERING FOOTPRINT\***



DIMENSIONS: MILLIMETERS

#### **GENERIC MARKING DIAGRAM\***



XXXXX = Specific Device Code = Assembly Location

WL = Wafer Lot ΥY = Year WW = Work Week = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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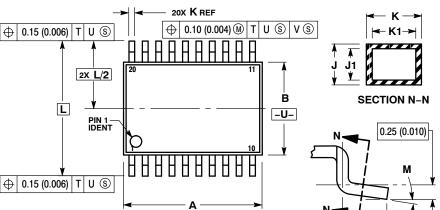
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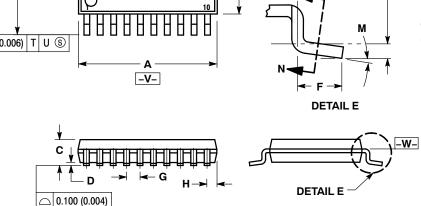
<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



#### TSSOP-20 WB CASE 948E ISSUE D

**DATE 17 FEB 2016** 





#### NOTES:

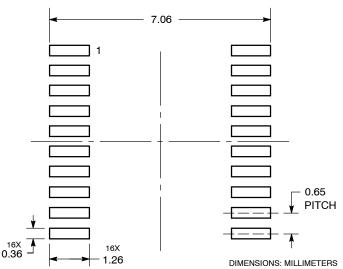
- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: MILLIMETER.
- 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
- FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K
- (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

  7. DIMENSION A AND B ARE TO BE
- DETERMINED AT DATUM PLANE -W-

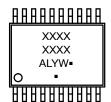
	MILLIN	IILLIMETERS INC		HES
DIM	MIN	MAX	MIN	MAX
Α	6.40	6.60	0.252	0.260
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.27	0.37	0.011	0.015
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40	BSC	0.252	BSC
M	0°	8°	0°	8°

#### **SOLDERING FOOTPRINT**

-T- SEATING



#### **GENERIC MARKING DIAGRAM\***



= Assembly Location

= Wafer Lot

= Year

= Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

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DESCRIPTION:	TSSOP-20 WB		PAGE 1 OF 1

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